

DN8899/SE/TE/S

Hall IC (Operating Temperature Range
 $T_{opr} = -40$ to $+100^{\circ}\text{C}$,
 Operating in Alternative Magnetic Field)

■ Overview

The DN8899/SE/TE/S is a combination of a Hall element, amplifier, Schmitt circuit, and stabilized power supply/temperature compensator integrated on an identical chip by using the IC technology. It amplifies Hall element output at the amplifier, converts into a digital signal through the Schmitt circuit, and drives the TTL or MOS IC directly.

■ Features

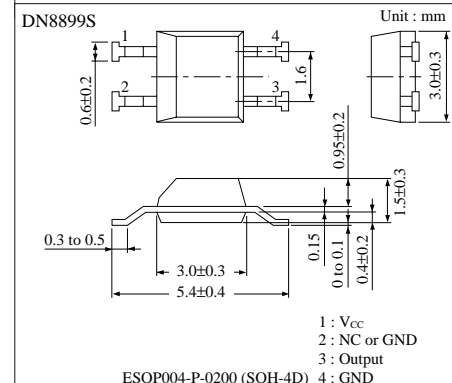
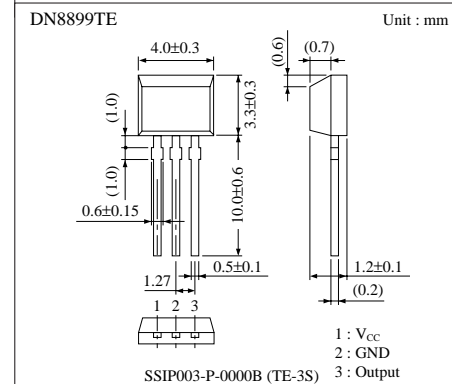
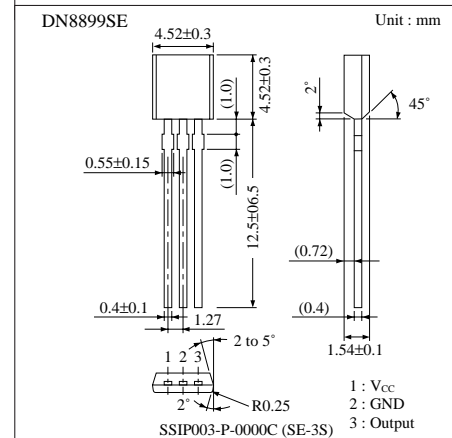
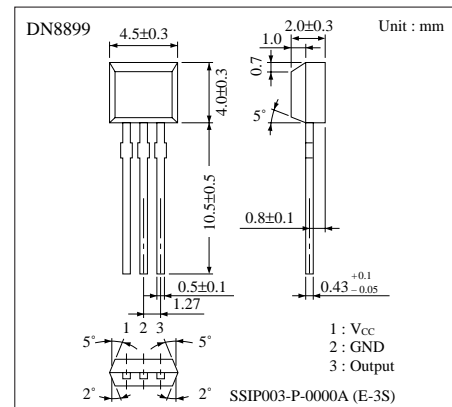
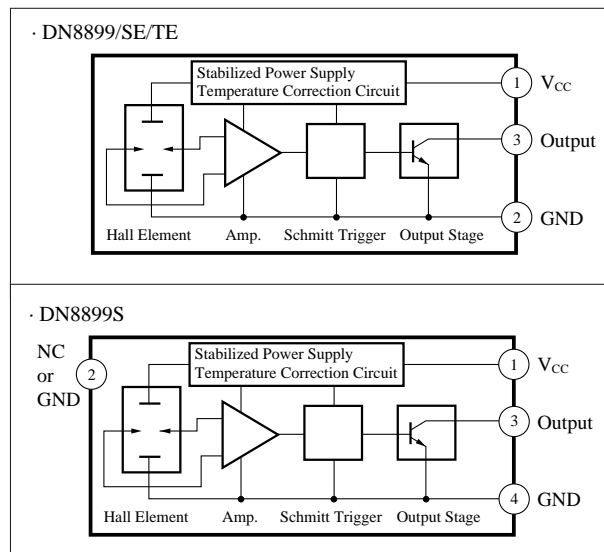
- High sensitivity and low drift
- Stable temperature characteristics due to the additional temperature compensator
- Wide operating supply voltage range ($V_{CC} = 4.5$ to 16V)
- Operating in alternative magnetic field
- TTL and MOS ICs directly drivable by output
- Semipermanent service life due to no contact parts
- Small change of the operating flux density against mechanical stress
- Output open collector
- "0" gauss point in the zero cross type hysteresis width

■ Applications

- Speed sensors
- Position sensors
- Rotation sensors
- Keyboard switches
- Microswitches

Note) This IC is not suitable for the car electric equipment.

■ Block Diagram



■ Absolute Maximum Ratings (Ta=25°C)

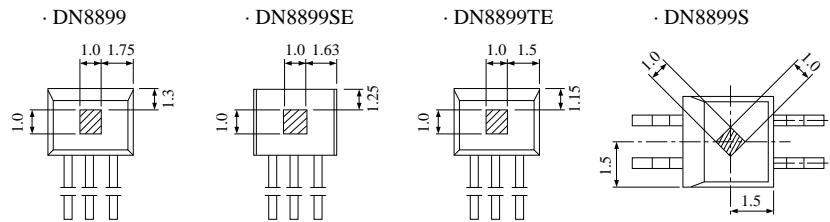
Parameter	Symbol	Rating	Unit
Supply voltage	V _{CC}	18	V
Supply current	I _{CC}	8	mA
Circuit current	I _O	20	mA
Power dissipation	P _D	150	mW
Operating ambient temperature	T _{opr}	-40 to +100	°C
Storage temperature	T _{stg}	-55 to +125	°C

■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Operating flux density	B ₁ (L→H)	V _{CC} =12V	-12	-6	-0.1	mT
	B ₂ (H→L)	V _{CC} =12V	0.1	6	12	mT
Hysteresis width	BW	V _{CC} =12V	7	10	—	mT
Low output voltage	V _{OL}	V _{CC} =4.5 to 16V, I _O =12mA, B=12mT	—	—	0.4	V
High output current	I _{OH}	V _{CC} =4.5 to 16V, V _O =16V, B=-12mT	—	—	10	μA
Supply current	I _{CC}	V _{CC} =16V	—	—	6	mA
		V _{CC} =4.5V	—	—	5.5	mA

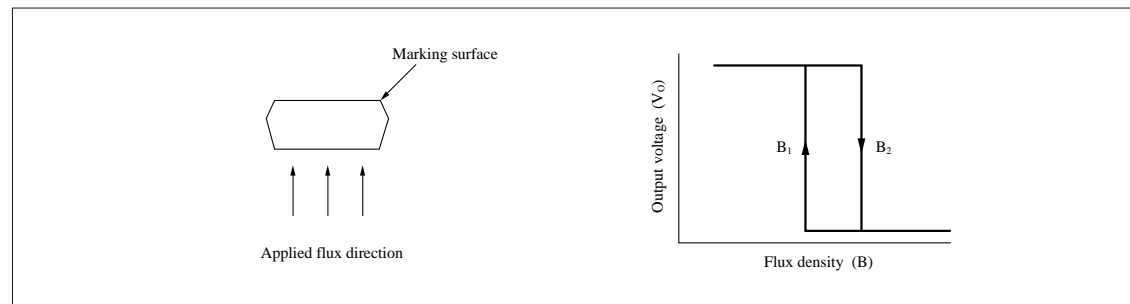
■ Hall Element Position

Unit : mm
The center of the Hall element is in the hatched area in the right figure.



Distance from package surface to sensor (mm)	DN8899	DN8899SE	DN8899TE	DN8899S
		0.7	0.42	0.4

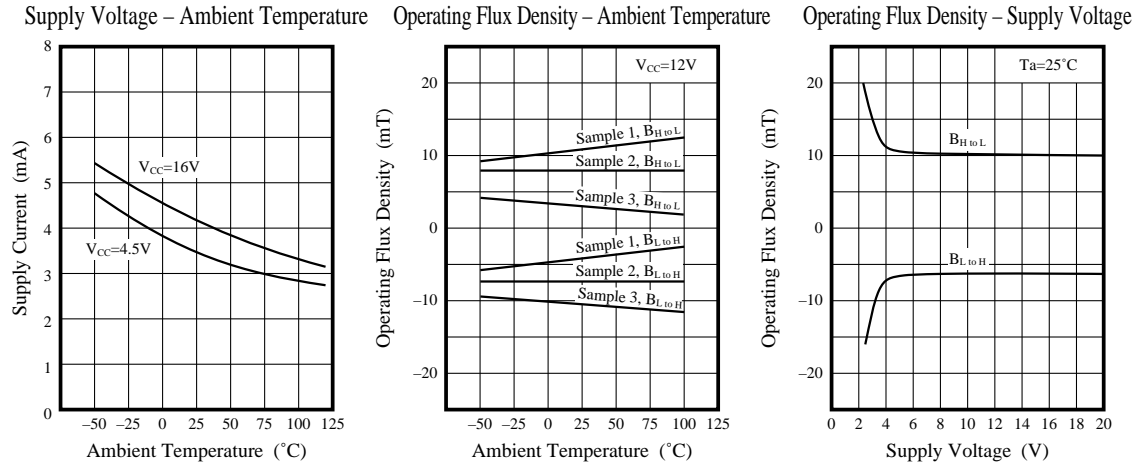
■ Flux-Voltage Conversion Characteristics



■ Supplementary Descriptions

1. Change of the operation magnetic flux density dose not depend on the supply voltage, because the stabilization power supply is built in. (only for the range ; $V_{CC}=4.5$ to 16V)
2. Change from "H" to "L" level increases the supply current by approx. 1mA.

■ Characteristics Curve



Output Low Level Voltage – Ambient Temperature

